

# InP Grating Etches

## Oxford PlasmaPro 100 Cobra 300

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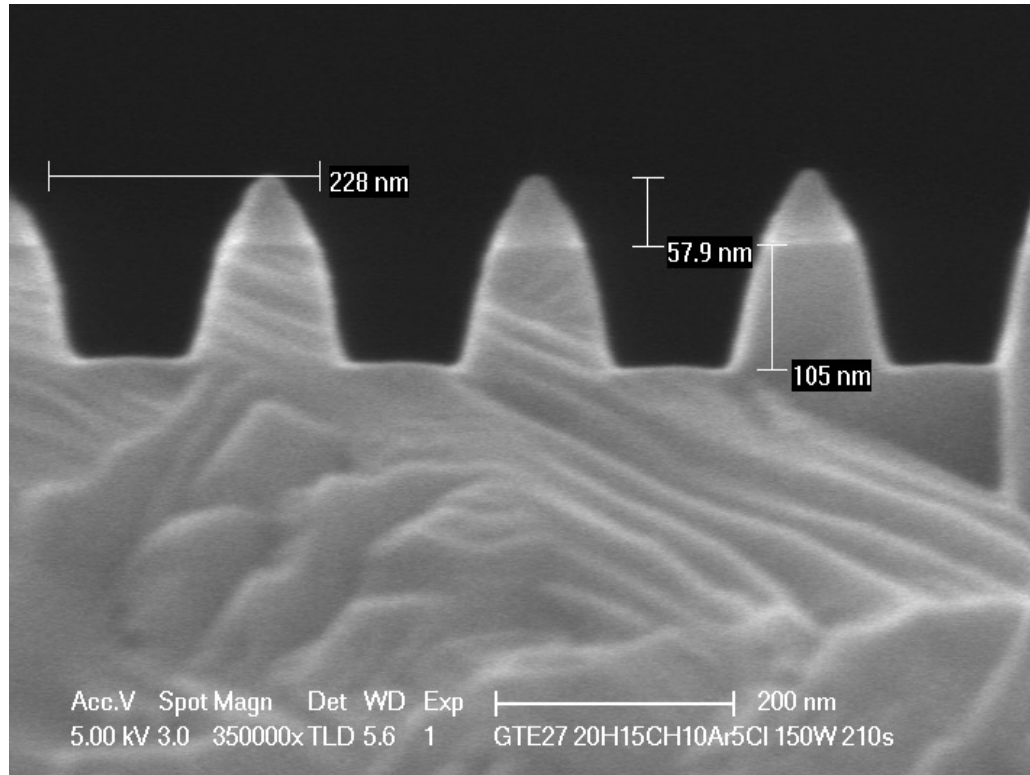
# The “standard” InP Grating recipe:

“Std InP Grating Etch - Cl<sub>2</sub>/CH<sub>4</sub>/H<sub>2</sub>/Ar 20C”

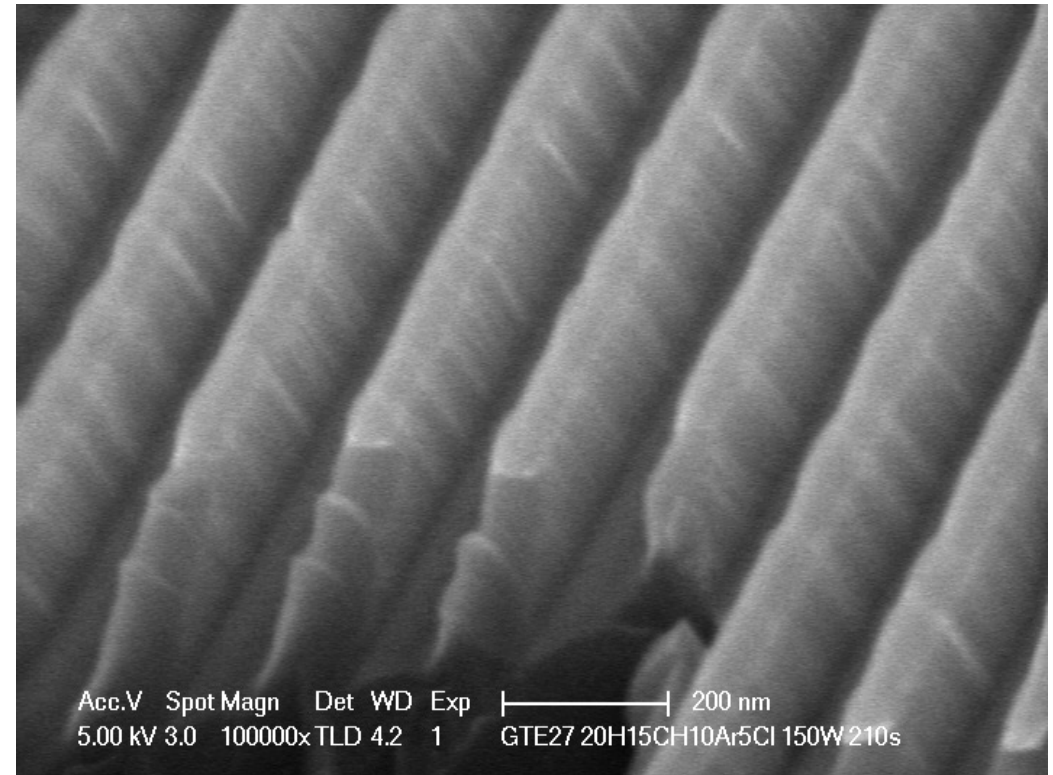
20°C table temp., 1cm piece on Si carrier, no mounting adhesive

2mT, RF=150W/ICP=100W; CH<sub>4</sub>=15/H<sub>2</sub>=20/Ar=10/Cl<sub>2</sub>=5 sccm; 3.5 min

**Sample from #4A, Etch rate=29.4  
nm/min, sidewall angle=77.7 degree**



**Bottom surface is smooth**



# Recipe Variations in following slides

- Development process – 30 etches performed to achieve best result
- Targeting:
  - Slightly non-vertical grating sidewall, for regrowth
  - no micro-trenching
  - Smooth etched surfaces (no pillars/micromasking etc.)

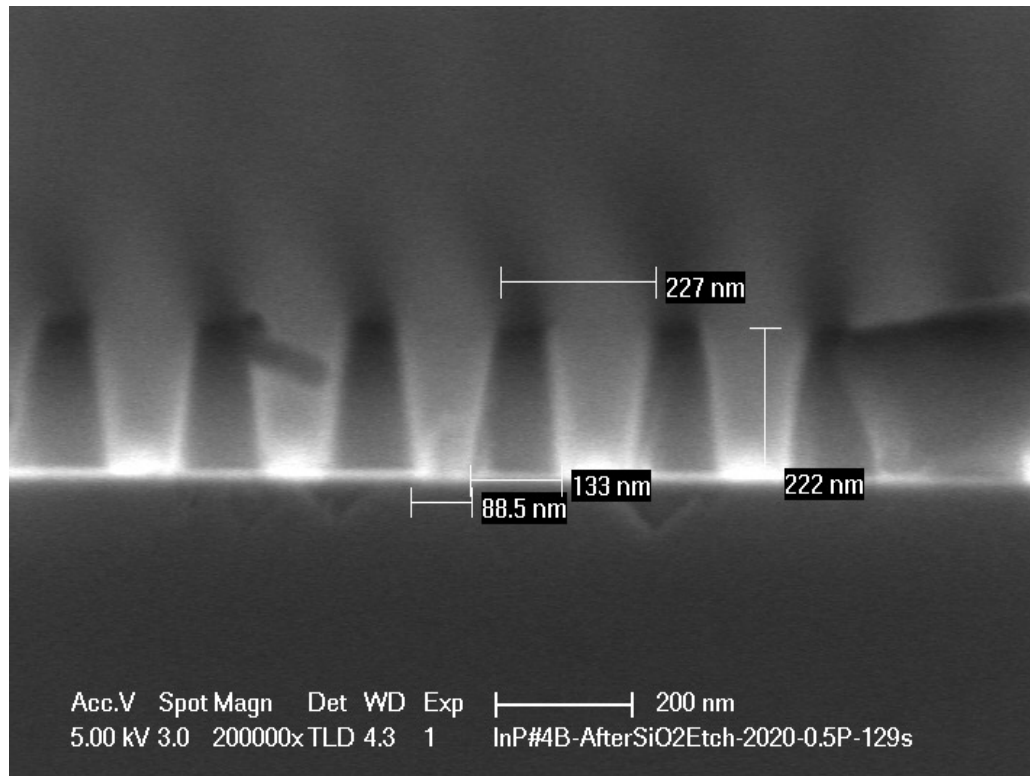
# InP Grating Etch at 20 C, PlasmaPro 100 Cobra

InP pieces

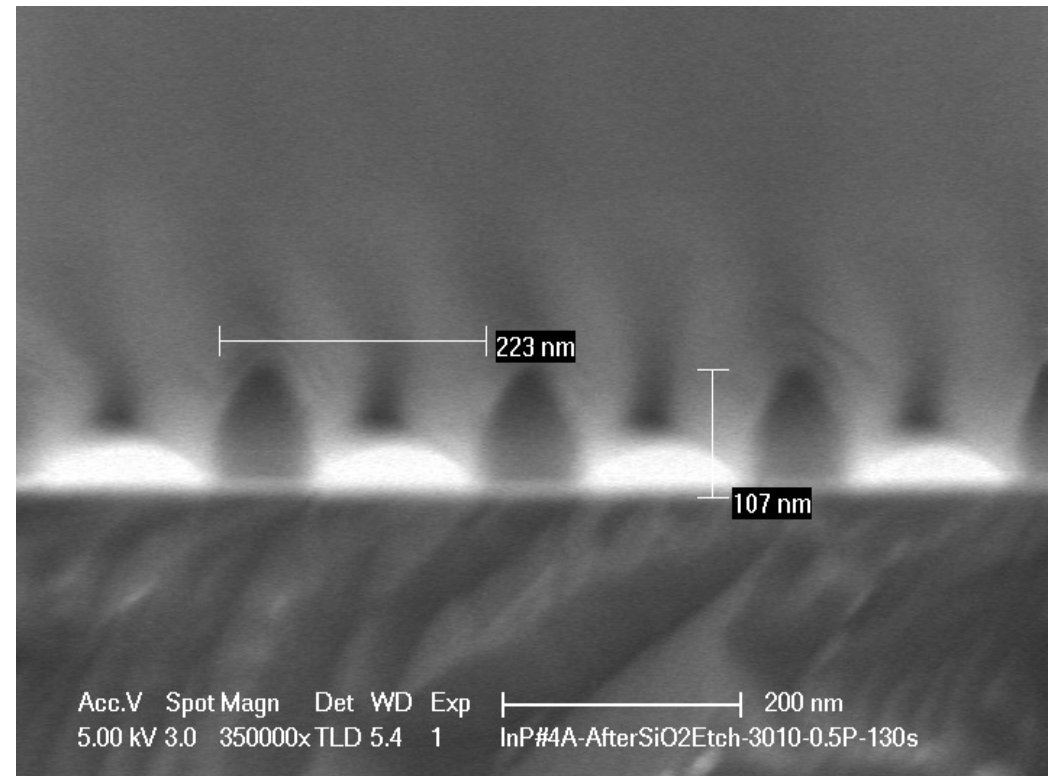
SiO<sub>2</sub> Hardmask patterned by Holography

100mm Silicon carrier wafer, no adhesive, rough side up

Grating Pattern (Holography and SiO<sub>2</sub> Etch) Quarter#4B

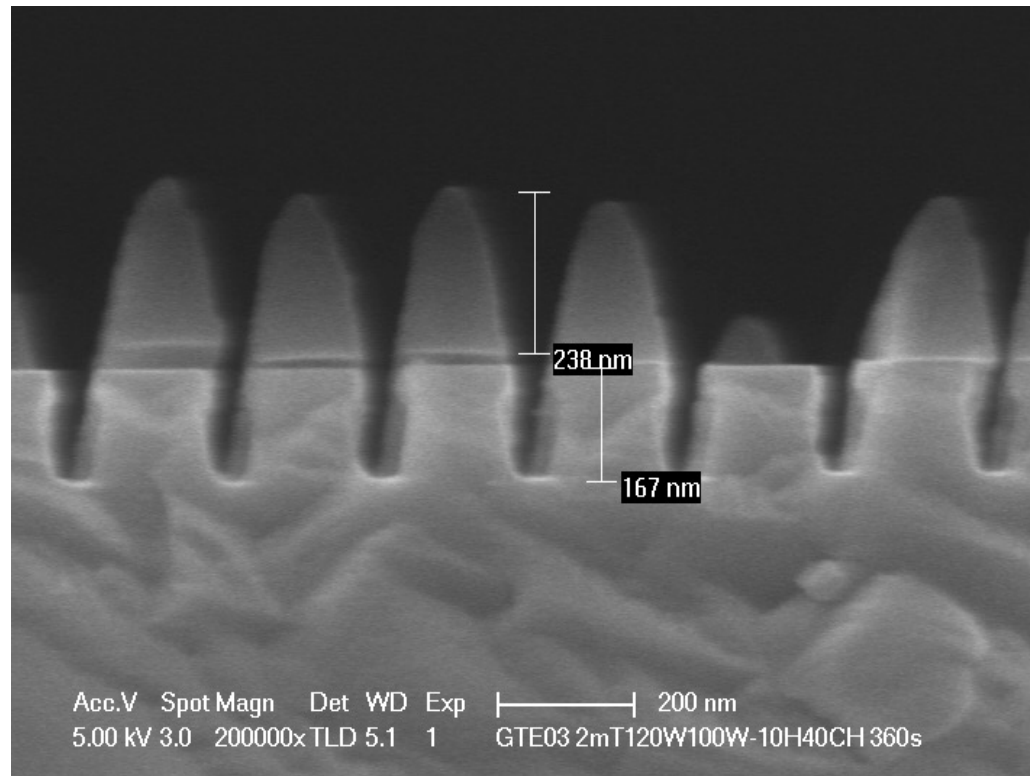


Grating Pattern (Holography and SiO<sub>2</sub> Etch) Quarter#4A

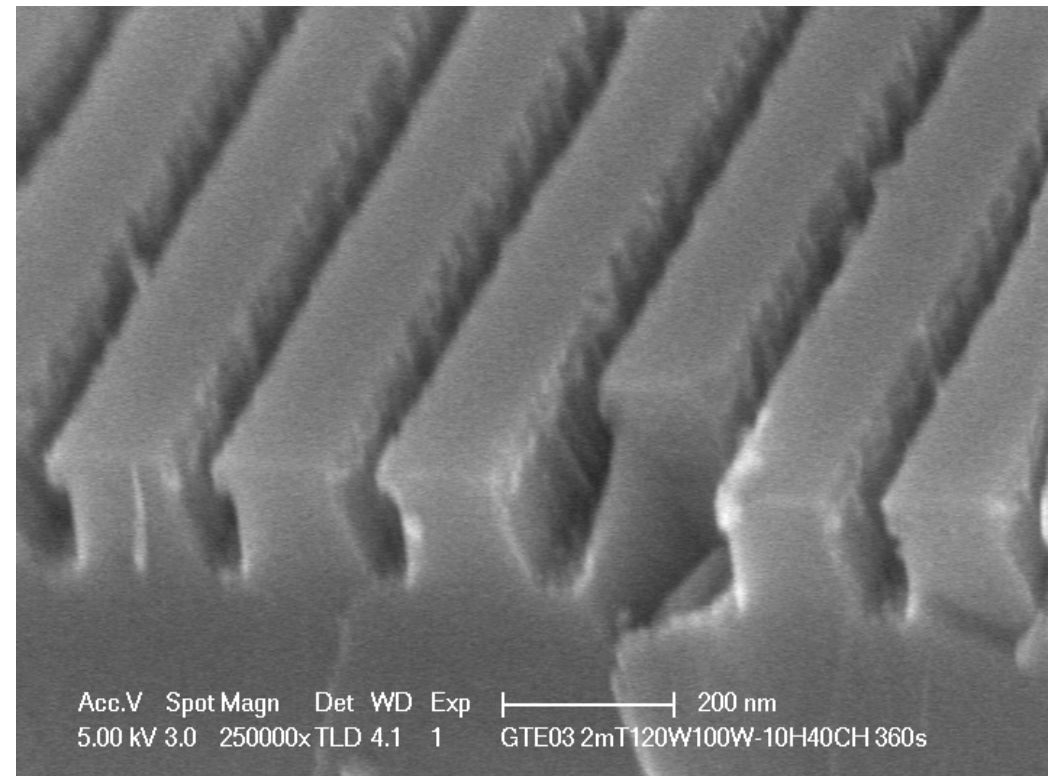


Oxford Recipe: 2mT, CH<sub>4</sub>/H<sub>2</sub>=40/10 sccm,  
120W(Bias)-100W(ICP), 6 min

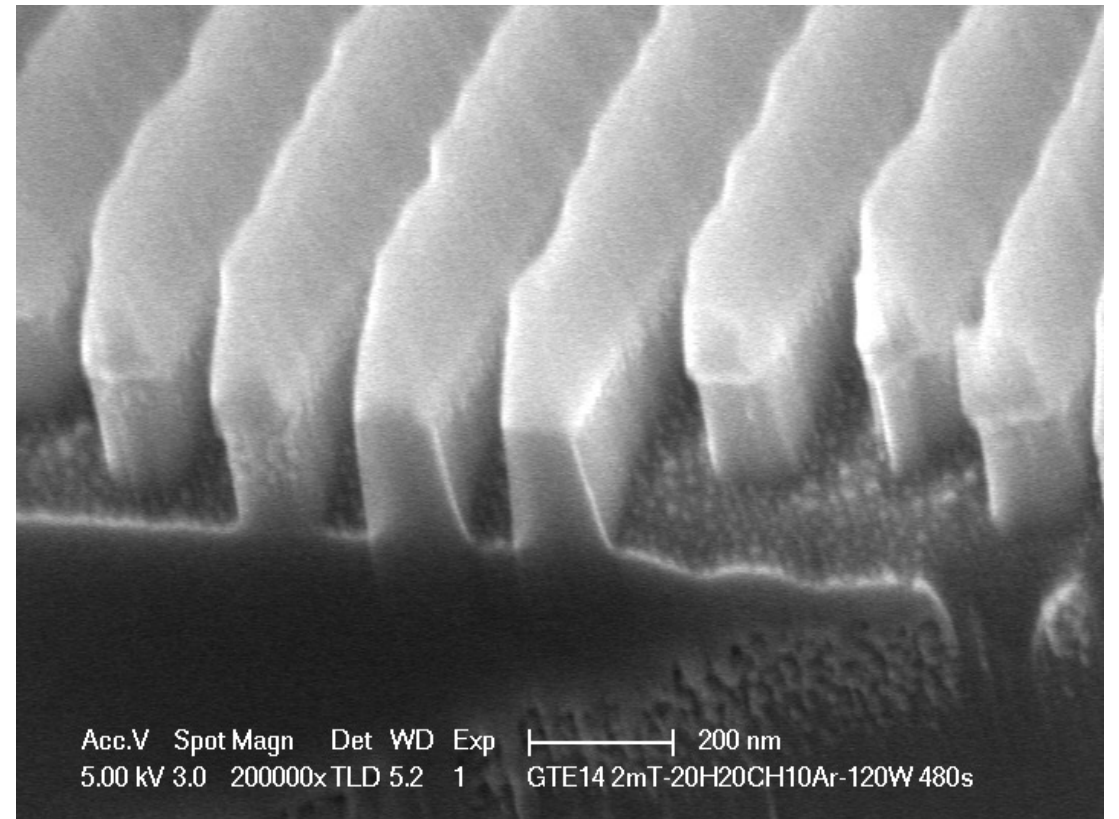
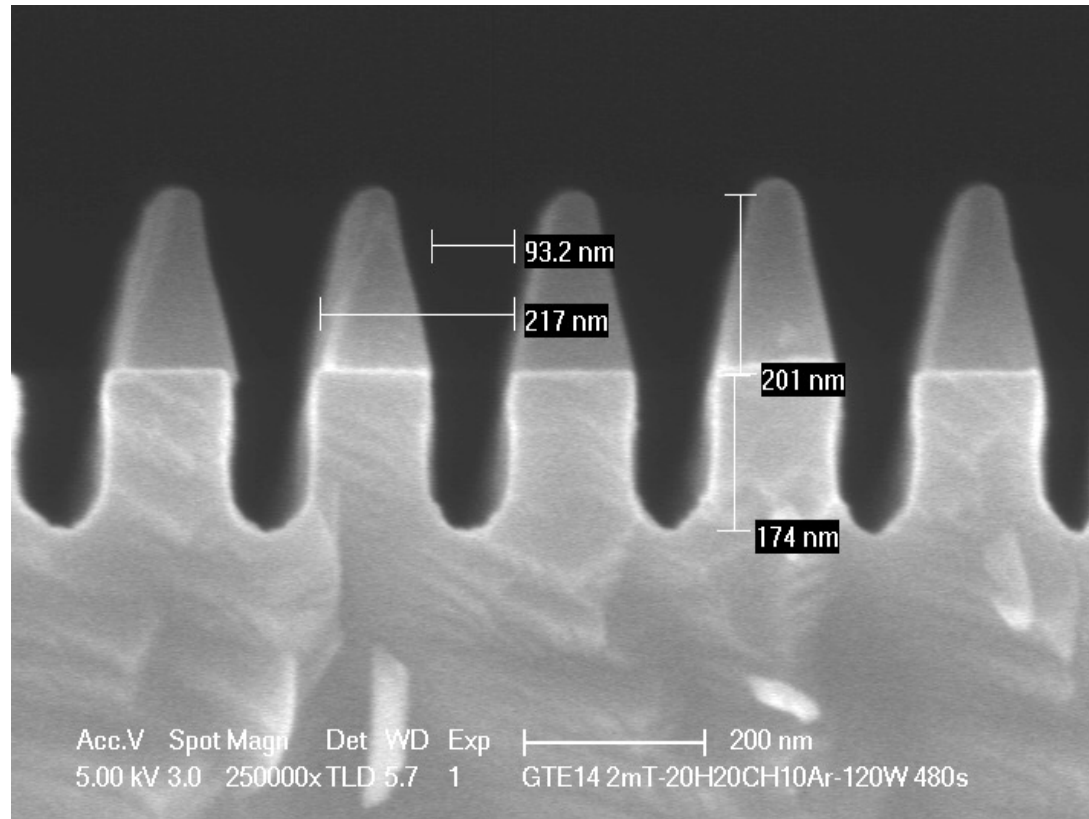
Using #4B



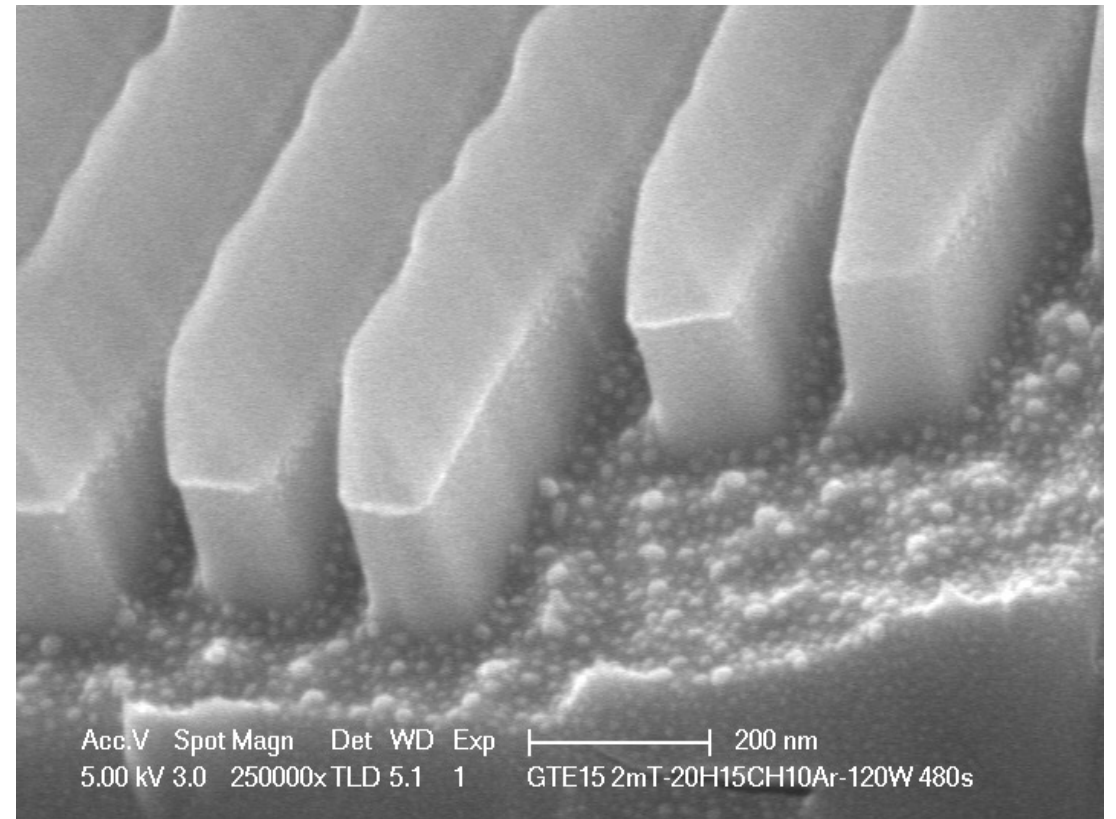
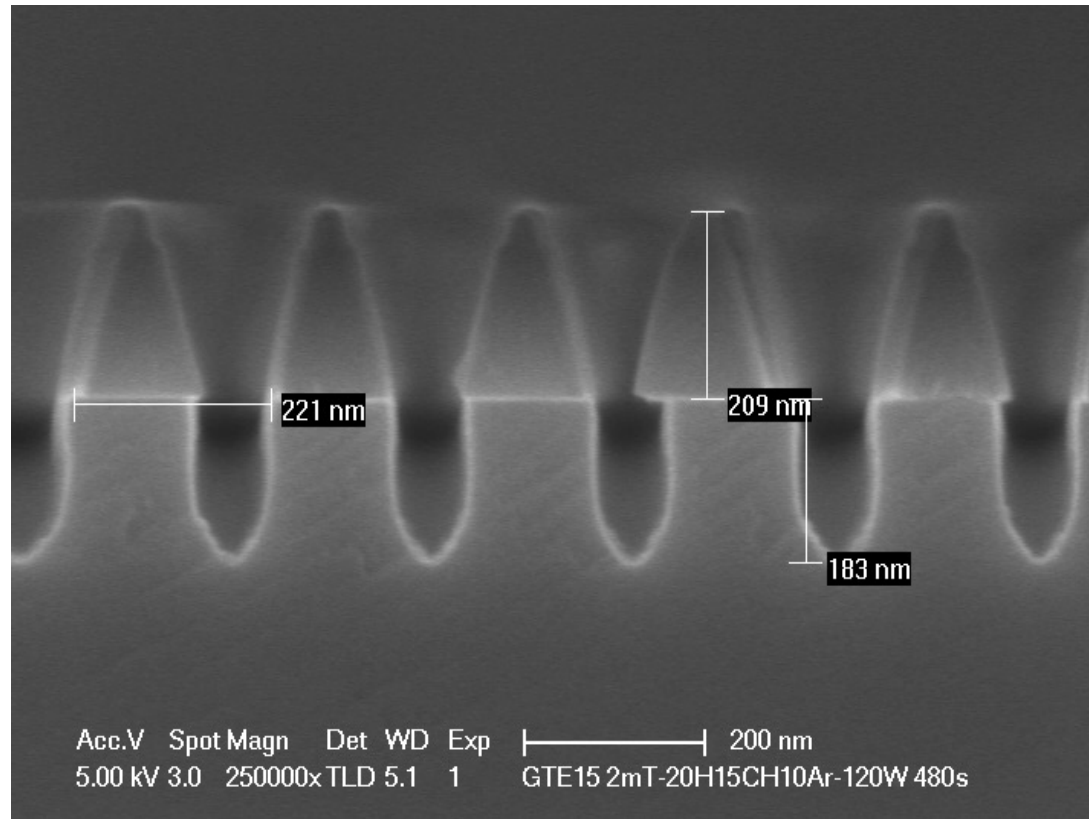
Issue: too much CH<sub>4</sub>, and polymer built up



Reducing CH4: 2mT, 120W-100W,  
CH4/H2/Ar=20/20/10 sccm, 8 min

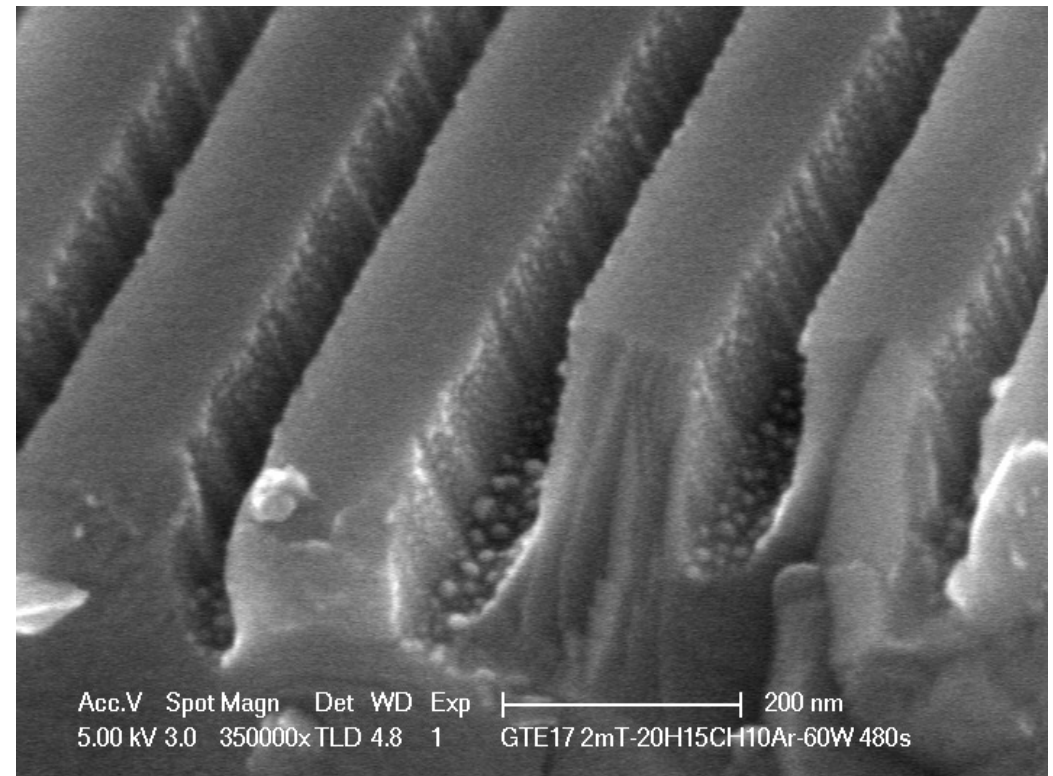
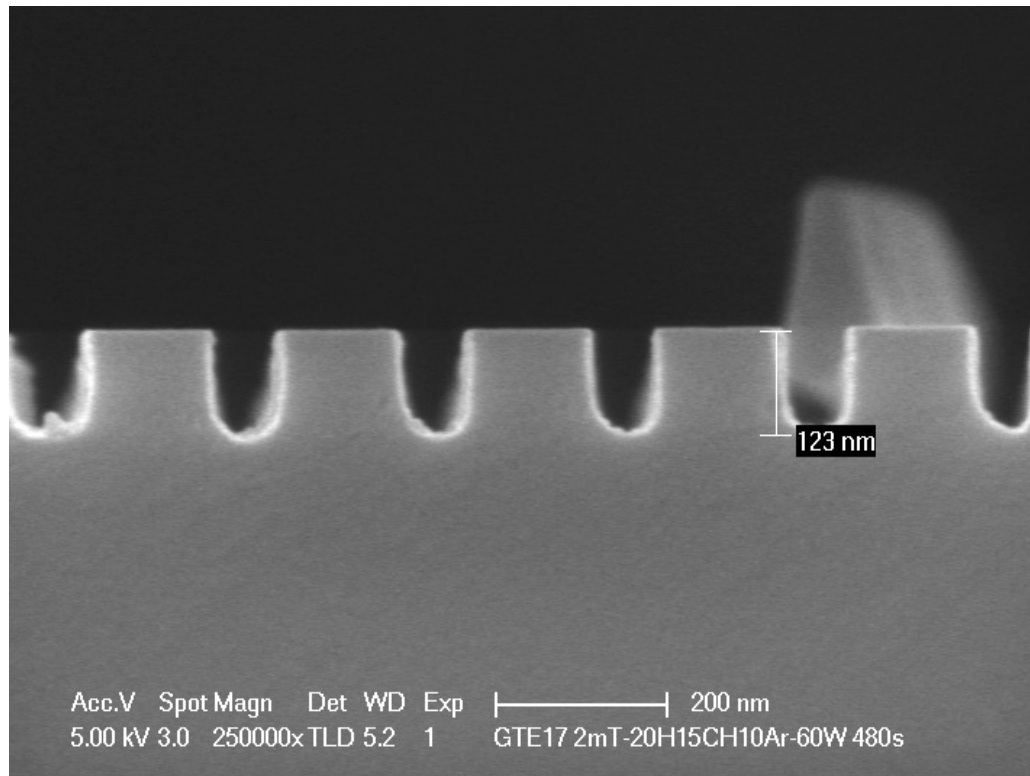


Further Reducing CH4: 2mT, 120W-100W,  
CH4/H2/Ar=15/20/10 sccm, 8 min



Reducing Bias: 2mT, 60W-100W,  
CH<sub>4</sub>/H<sub>2</sub>/Ar=15/20/10 sccm, 8 min

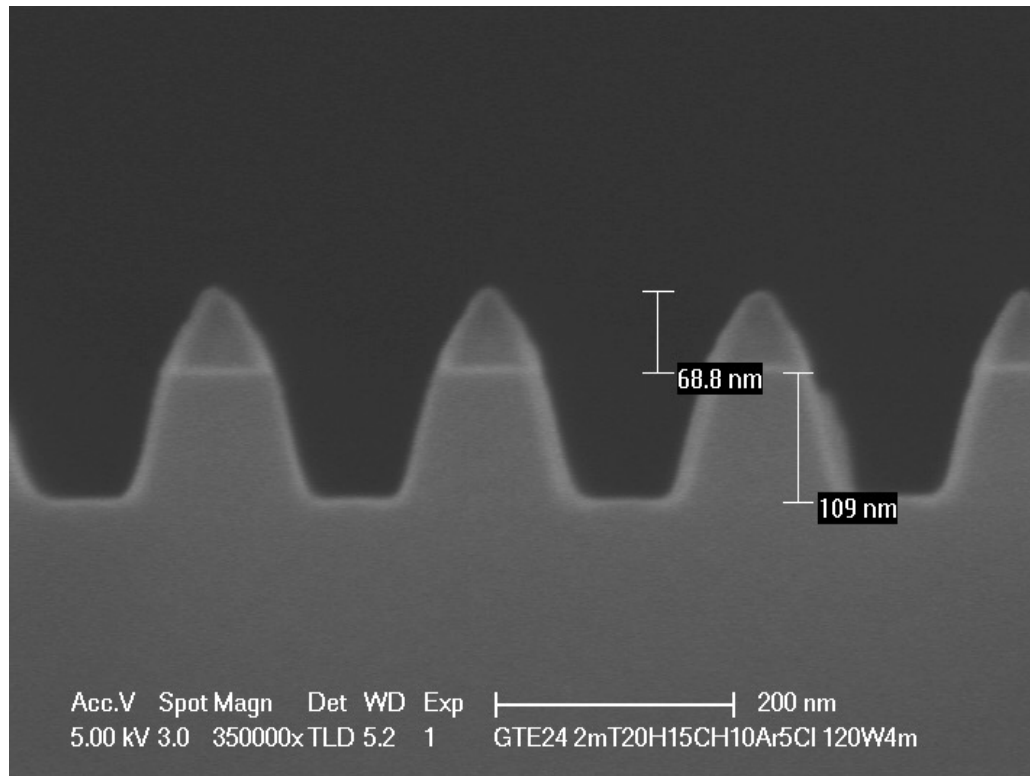
**The bottom roughness still there!**



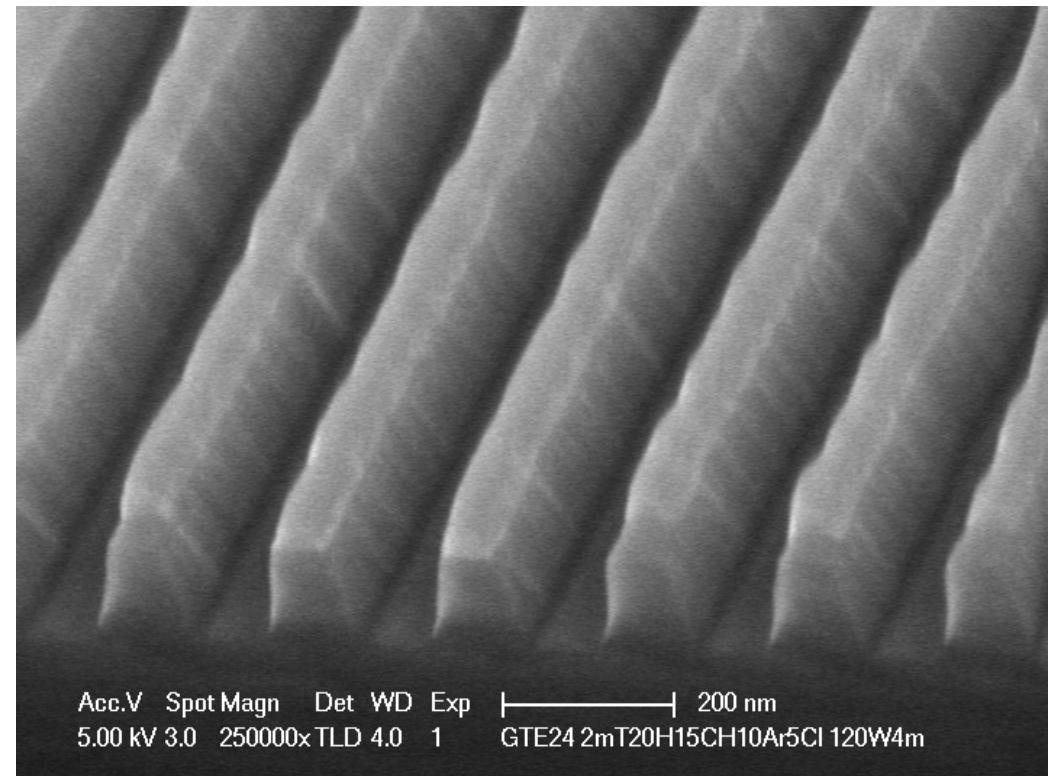


Adding Cl<sub>2</sub>: 2mT, 120W-100W,  
CH<sub>4</sub>/H<sub>2</sub>/Ar/Cl<sub>2</sub>=15/20/10/5 sccm, 4min

Sample from #4A, Etch Rate=27.6  
nm/min, sidewall angle=74.4 degree



Bottom roughness gone!



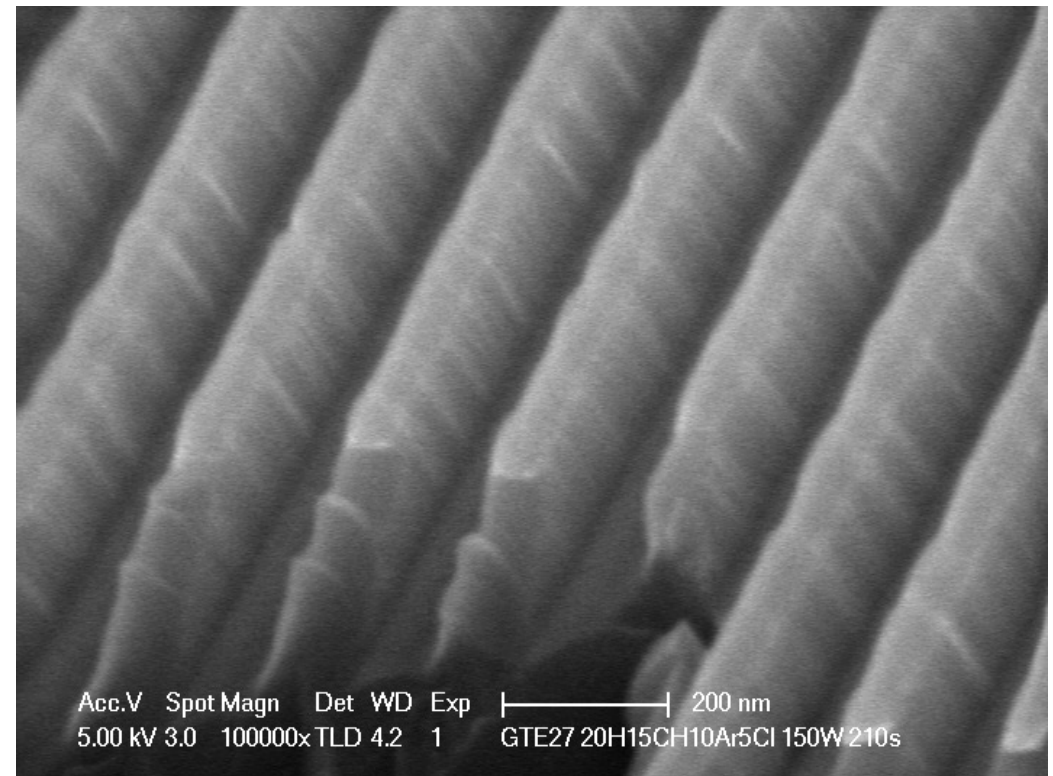
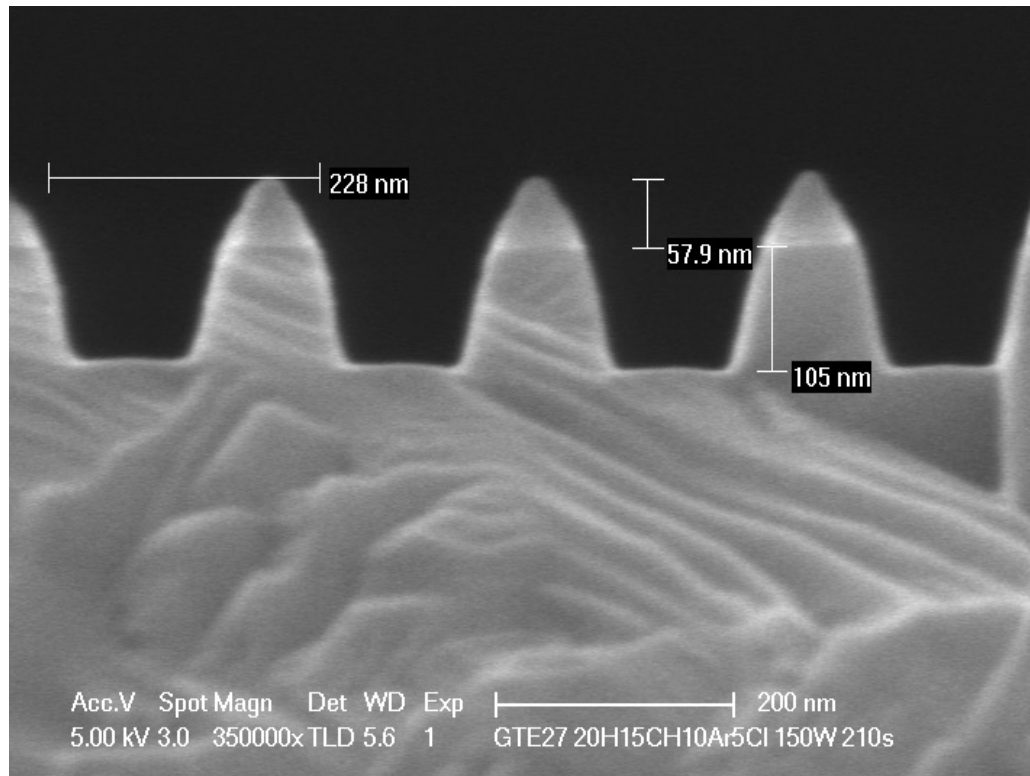


This is the "standard" InP Grating recipe

Increasing Bias: 2mT, 150W-100W  
CH<sub>4</sub>/H<sub>2</sub>/Ar/Cl<sub>2</sub>=15/20/10/5 sccm, 3.5 min

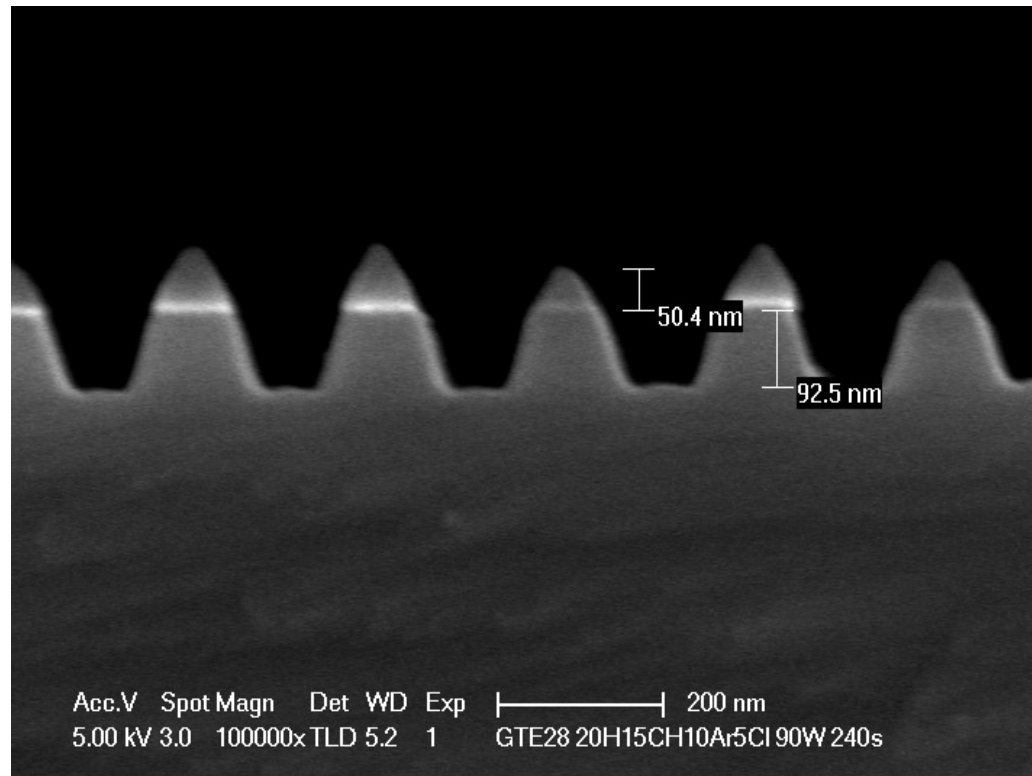
Sample from #4A, Etch rate=29.4  
nm/min, sidewall angle=77.7 degree

Bottom roughness gone!



Decreasing Bias: 2mT, 90W-100W,  
CH<sub>4</sub>/H<sub>2</sub>/Ar/Cl<sub>2</sub>=15/20/10/5 sccm, 4 min

Sample from #4A, Etch Rate=24.3  
nm/min



Bottom roughness gone!

